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Supplementary Information: Electrical properties of disordered films of van der Waals semiconductor WS₂ on paper

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13 The supplementary information contains a video about the film deposition and a section about the random resistor14 network model.

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16 Resistors network solver

- 17 Fig. S1 show four different resistor networks generated as artificial Brownian surfaces through synthetic surface
- 18 generator in Gwyddion 2.64 with different Hurst exponents and stationarity scale to control the amount of high
- 19 (spatial) frequency noise.

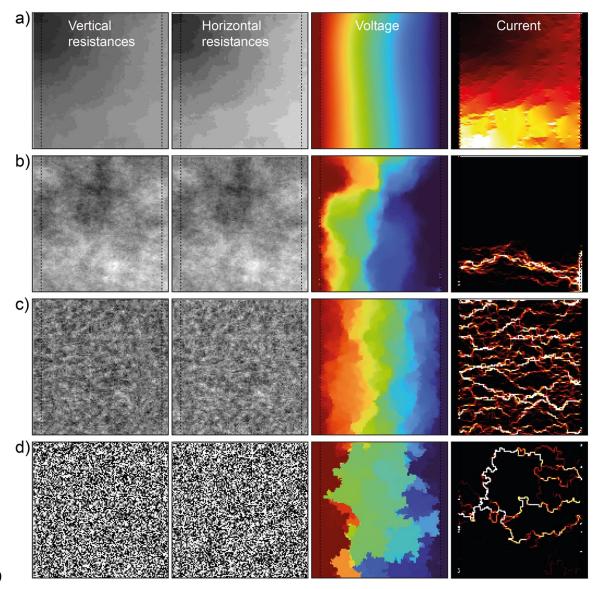


Figure S1: Additional random resistance networks model. a) First and second column: RRN composed of 120x120 resistors, respectively vertically aligned resistors (left) and horizontally aligned ones (right). Black corresponds to higher resistance values and white to lower ones. Third column: calculated voltage across the RRN with boundary conditions V=1 V on the far-left side (in red) and V=0 V on the far-right side (in blue). Fourth column: current density calculated from the resistance and voltage maps. b-d) Same as panel (a) but for increasing high frequency random noise in the resistors networks (high frequency noise increases from top to bottom).